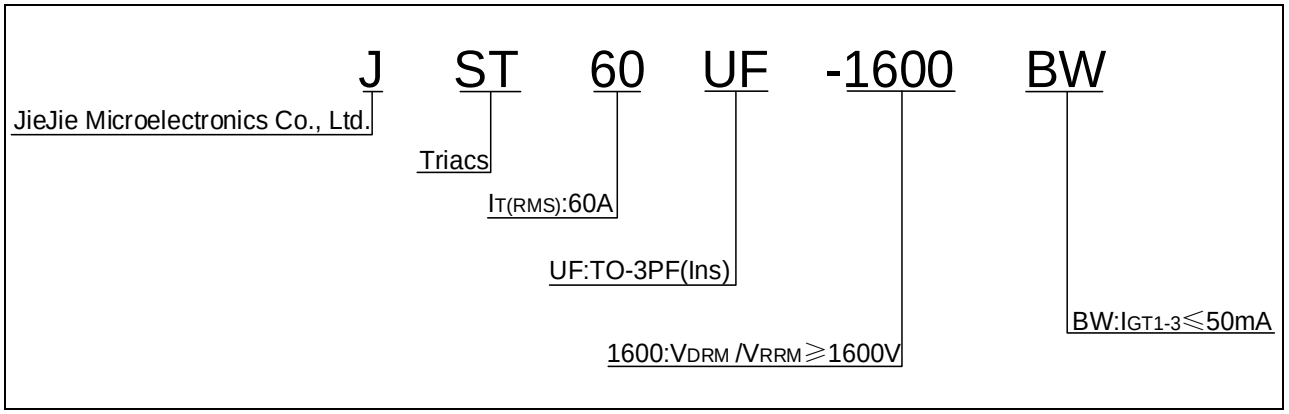
Average gate power dissipation (T_j=125℃)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25℃; non-repetitive,off-state;FIG.7)	V_{pp}	2	kV

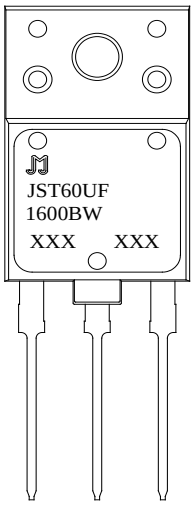
(T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	Ⅰ-Ⅱ-Ⅲ	MAX.	50	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j=125℃ R_L =3.3k	Ⅰ-Ⅱ-Ⅲ	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	Ⅰ-Ⅲ	MAX.	120	mA
		Ⅱ		120	
I_H	I_T =1A		MAX.	80	mA
dV/dt	V_D=1070V Gate Open T_j=125℃		MIN.	1500	V s
(dI/dt)c	j=125℃		MIN.	28	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25℃		TYP.	7	s
t_{off}				100	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =85A t_p=380 s	T_j=25℃	1.7	V
V_{TO}	Threshold voltage	T_j=125℃	0.68	V
R_D	Dynamic resistance	T_j=125℃	27	m
I_{DRM}	V_D=$V_{DRM}$$V_R$ =V_{RRM}	T_j=25℃	15	A
I_{RRM}		T_j=125℃	10	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.21	℃/W
$R_{th(j-a)}$	junction to ambient (AC)	40	℃/W


J
ST
60
UF
-1600
BW
JieJie Microelectronics Co., Ltd.
Triacs
IT(RMS):60A
UF:TO-3PF(Ins)
1600:VDRM /VRRM≥1600V
BW:IGT1-3≤50mA


JST60UF
1600BW
XXX XXX

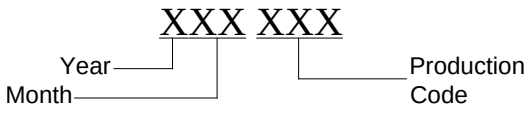

XXX XXX
Year
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Production
Code

FIG.1: Maximum power dissipation versus RMS on-state current

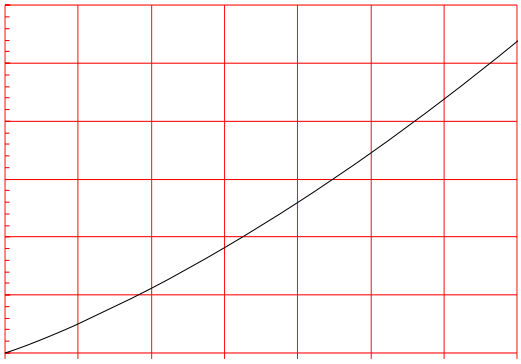


FIG.2: RMS on-state current versus case temperature

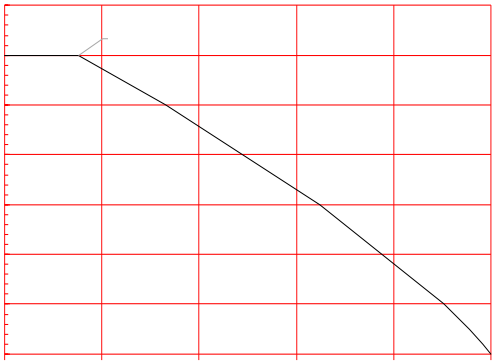


FIG.3: Surge peak on-state current versus number of cycles

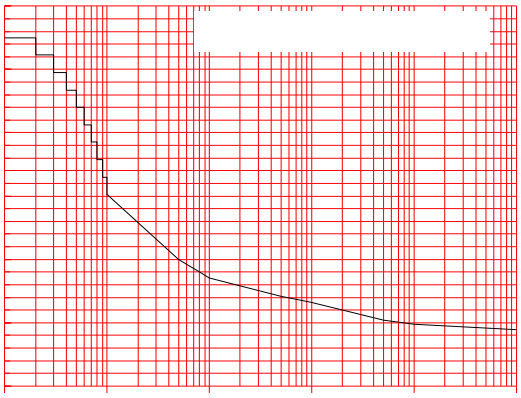


FIG.4: On-state characteristics

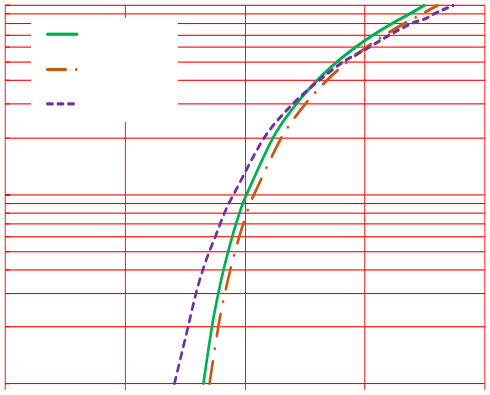


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2

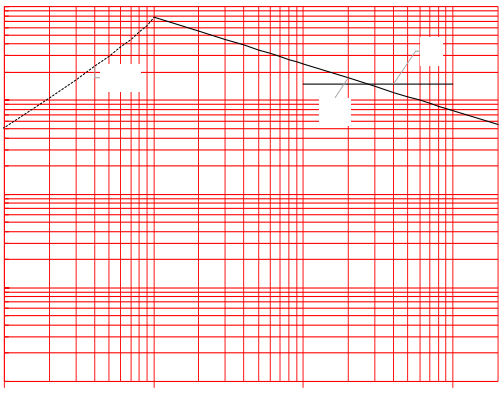


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

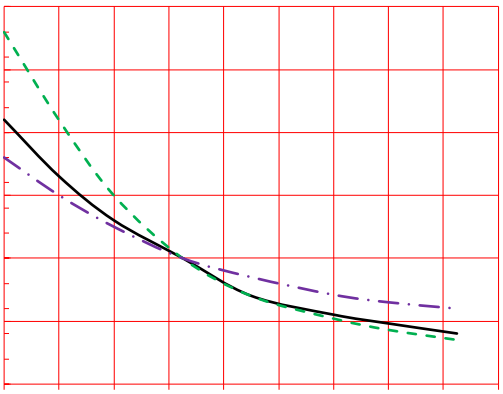
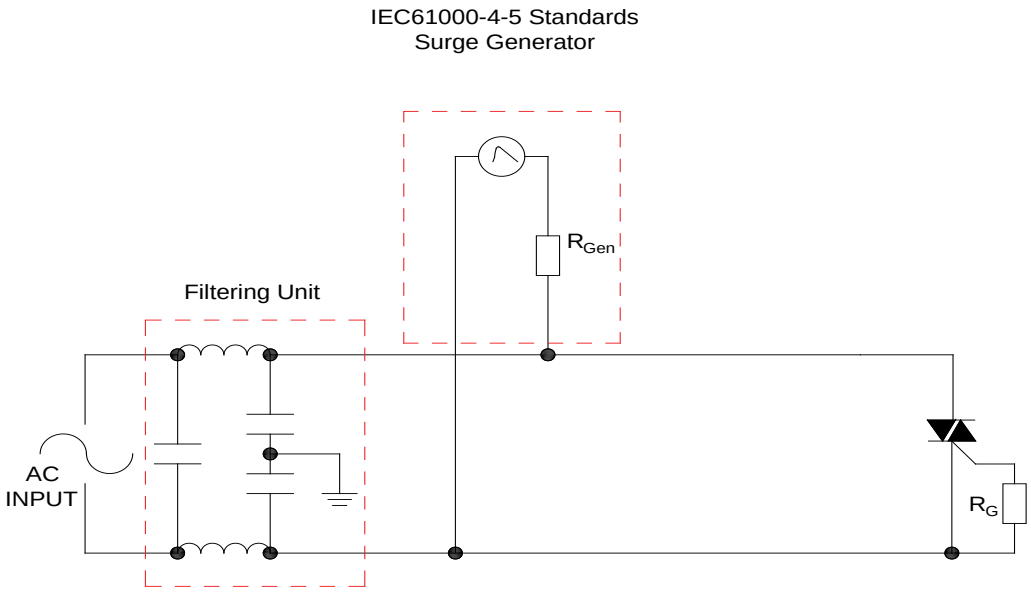


FIG.7：Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie

Order code	Voltage V_{DRM}/V_{RRM}(V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST60UF-1600BW	1600	50	TO-3PF(Ins)	30	Tube

Document Revision History

Date	Revision	Changes
Jul.9, 2025	A.1.0	Last updated



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